10-FZ073BA030SM07-M575L308

datasheet

flowBOOST 0 triple **650 V / 30 A**

Topology features

- Kelvin Emitter for improved switching performance
- Integrated DC capacitor
- Temperature sensor
- Triple Booster

Component features

- High efficiency in hard switching and resonant topologies
- High speed switching
- Low gate charge

Housing features

- Base isolation: Al_2O_3
- Clip-in, reliable mechanical connection, qualified for wave soldering
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Solder pin

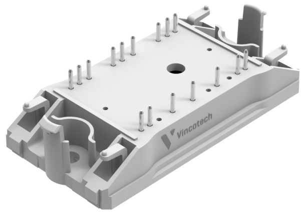
Target applications

- Charging Stations
- Power Supply
- Solar Inverters
- UPS

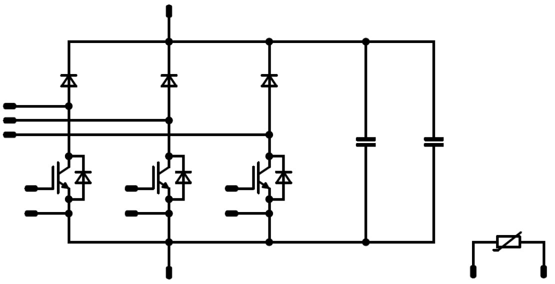
Types

- 10-FZ073BA030SM07-M575L308

flow 0 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Boost Switch					
Collector-emitter voltage	V_{CES}			650	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	32	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		90	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	60	W
Gate-emitter voltage	V_{GES}			±20	V
Maximum junction temperature	T_{jmax}			175	°C
Boost Diode					
Peak repetitive reverse voltage	V_{RRM}			650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	24	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		75	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 25 °C	142	A
Surge current capability	I^2t			100	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	62	W
Maximum junction temperature	T_{jmax}			175	°C
Boost Sw. Protection Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	38	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	200	A
Surge current capability	I^2t			200	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	46	W
Maximum junction temperature	T_{jmax}			150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Capacitor (DC)					
Maximum DC voltage	V_{MAX}			630	V
Operation Temperature	T_{op}			-55 ... 150	°C
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage	t_p = 1 min	2500	V
Creepage distance				>12,7	mm
Clearance				>12,7	mm
Comparative Tracking Index	CTI			≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0003	25	3,3	4	4,7	V
Collector-emitter saturation voltage	V_{CEsat}		15		30	25 125 150		1,67 1,8 1,84	2,22[1]	V
Collector-emitter cut-off current	I_{CES}		0	650		25			40	µA
Gate-emitter leakage current	I_{GES}		20	0		25			120	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		2100		pF
Reverse transfer capacitance	C_{res}	f = 1 Mhz	0	25		25		7,7		pF
Gate charge	Q_g	V_{CC} = 520 V	15		30	25		70		nC
Thermal										
Thermal resistance junction to sink [2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,57		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/15	400	30	25 125 150		21,12 20,48 20,16		ns
Rise time	t_r	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/15	400	30	25 125 150		9,28 10,24 10,56		ns
Turn-off delay time	$t_{d(off)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/15	400	30	25 125 150		134,4 151,68 156,8		ns
Fall time	t_f	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/15	400	30	25 125 150		4,96 10,39 12,31		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,051 µC Q_{rFWD}=0,049 µC Q_{rFWD}=0,05 µC	0/15	400	30	25 125 150		0,335 0,34 0,347		mWs
Turn-off energy (per pulse)	E_{off}		0/15	400	30	25 125 150		0,148 0,262 0,292		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Diode										
Static										
Forward voltage	V_F				16	25 125 150		1,49 1,75 1,87	1,8(1)	V
Reverse leakage current	I_R	V_r = 650 V				25		20	102	μA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,54		K/W
Dynamic										
Peak recovery current	I_{RM}	d*i*/d*t*=3122 A/μs d*i*/d*t*=2852 A/μs d*i*/d*t*=2764 A/μs	0/15	400	30	25 125 150		9,5 9,2 9,07		A
Reverse recovery time	t_{rr}					25 125 150		8,4 8,68 8,8		ns
Recovered charge	Q_r					25 125 150		0,051 0,049 0,05		μC
Reverse recovered energy	E_{rec}					25 125 150		$9{,}153\times10^{-3}$ $8{,}946\times10^{-3}$ $9{,}178\times10^{-3}$		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		2953 2573 2532		A/μs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Sw. Protection Diode										
Static										
Forward voltage	V_F				18	25 125 150		1,06 0,994 0,973	1,5[1]	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 1000	µA
Thermal										
Thermal resistance junction to sink [2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,54		K/W
Capacitor (DC)										
Static										
Capacitance	C	DC bias voltage = 0 V				25		33		nF
Tolerance							-5		5	%
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

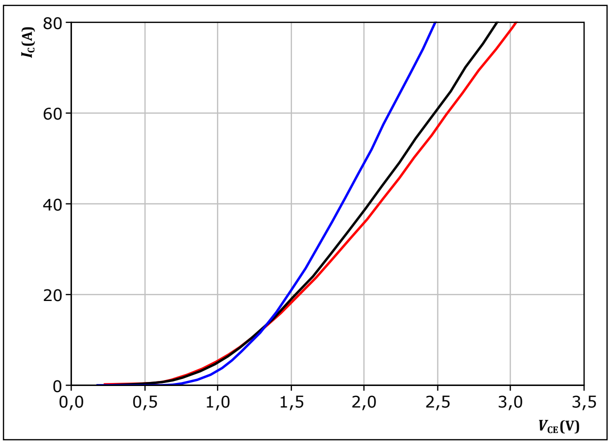
[1] Value at chip level
[2] Only valid with pre-applied Vincotech thermal interface material.

Boost Switch Characteristics

figure 1. IGBT

Typical output characteristics

I_C = f(V_{CE})



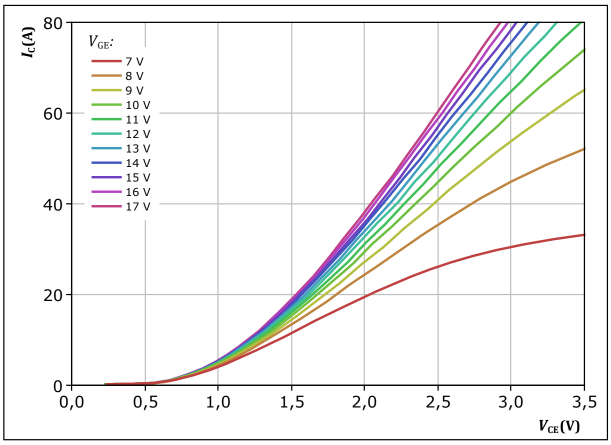
t_p =	250	µs
V_{GE} =	15	V

T_j: 25 °C, 125 °C, 150 °C

figure 2. IGBT

Typical output characteristics

I_C = f(V_{CE})



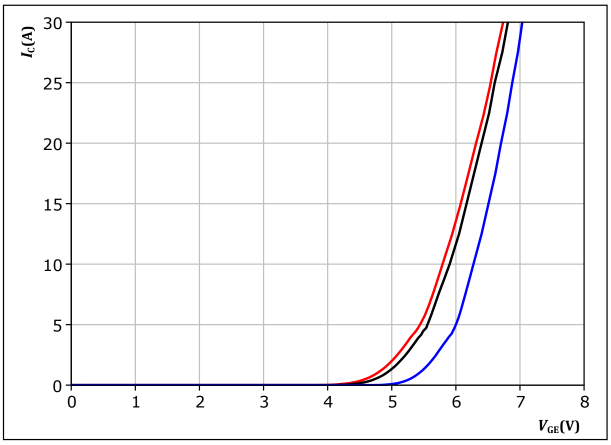
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

I_C = f(V_{GE})



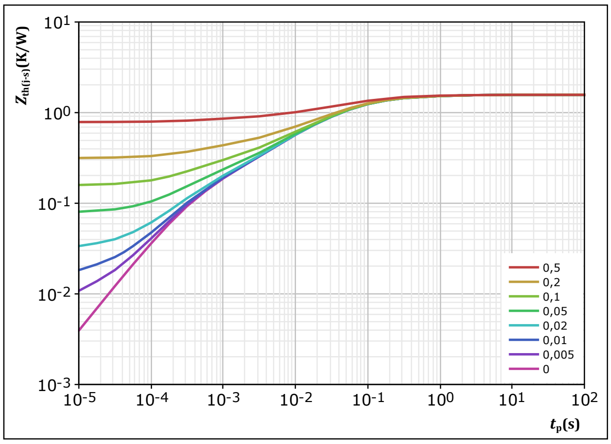
t_p =	250	µs
V_{CE} =	10	V

T_j: 25 °C, 125 °C, 150 °C

figure 4. IGBT

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,572 K/W

IGBT thermal model values

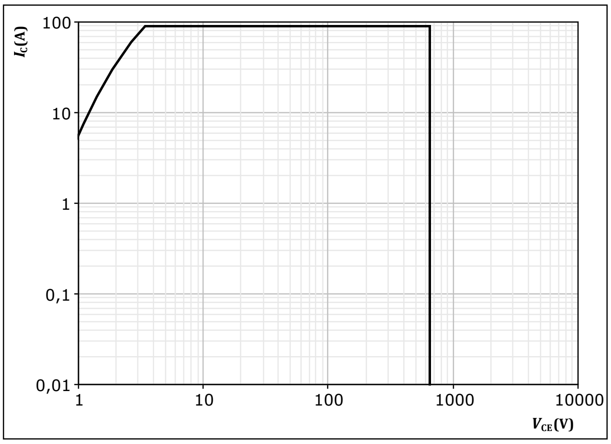
R (K/W)	τ (s)
7,66E-02	1,73E+00
2,00E-01	2,58E-01
6,54E-01	5,93E-02
3,77E-01	1,31E-02
1,51E-01	2,99E-03
1,13E-01	3,69E-04

Boost Switch Characteristics

figure 5.	IGBT

Safe operating area

$I_C = f(V_{CE})$



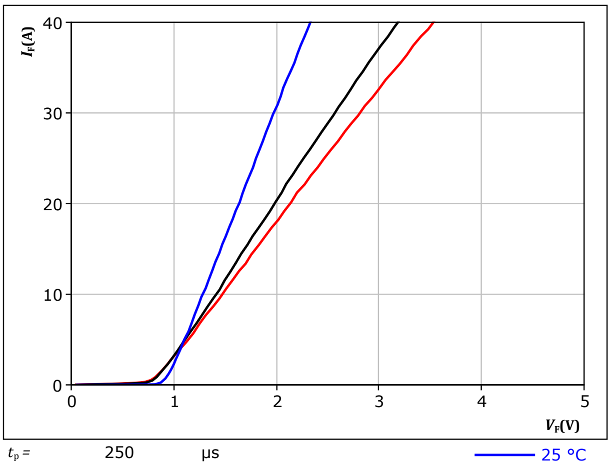
D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

Boost Diode Characteristics

figure 6. **FWD**

Typical forward characteristics

I_F = f(V_F)



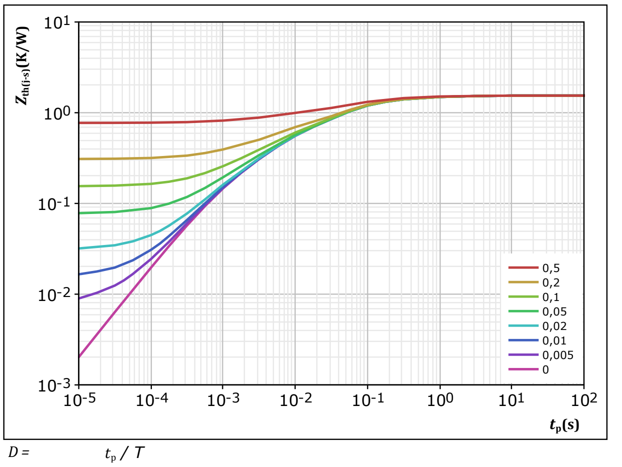
t_p = 250 μs

T_j: 25 °C, 125 °C, 150 °C

figure 7. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,543 K/W

FWD thermal model values

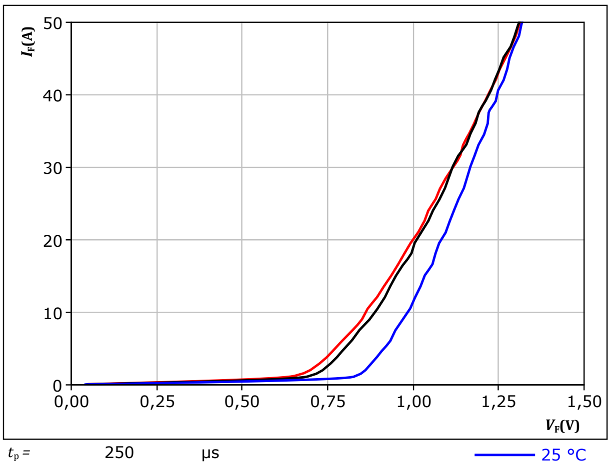
R (K/W)	τ (s)
8,00E-02	2,02E+00
2,86E-01	2,25E-01
7,15E-01	4,66E-02
3,66E-01	5,33E-03
9,56E-02	8,10E-04

Boost Sw. Protection Diode Characteristics

figure 8. **Rectifier**

Typical forward characteristics

$I_F = f(V_F)$



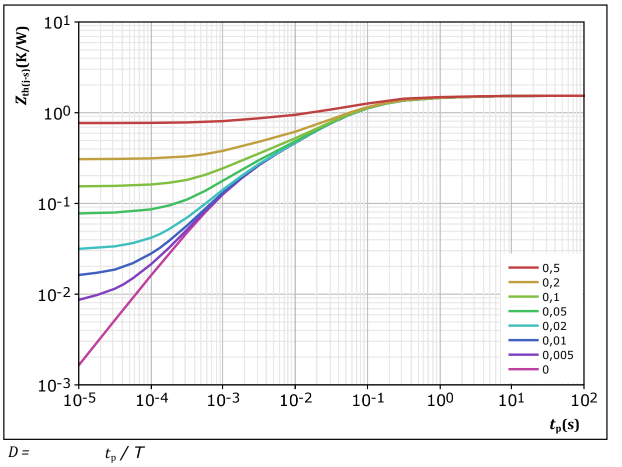
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 9. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,537 K/W

Rectifier thermal model values

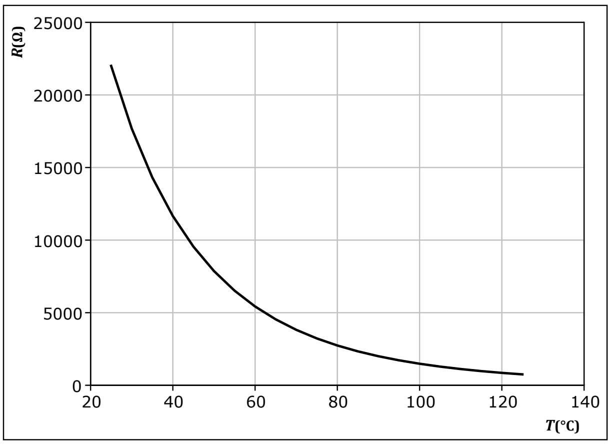
R (K/W)	τ (s)
7,03E-02	4,42E+00
2,01E-01	4,56E-01
7,63E-01	7,09E-02
3,40E-01	1,14E-02
1,63E-01	1,31E-03

Thermistor Characteristics

figure 10.	Thermistor

Typical NTC characteristic as function of temperature

R_T = f(T)

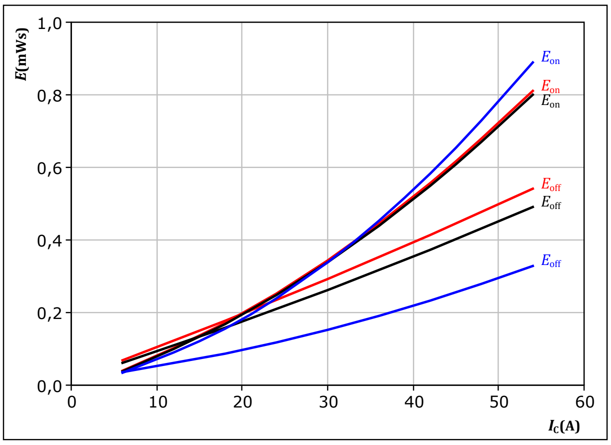


Boost Switching Characteristics

figure 11. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



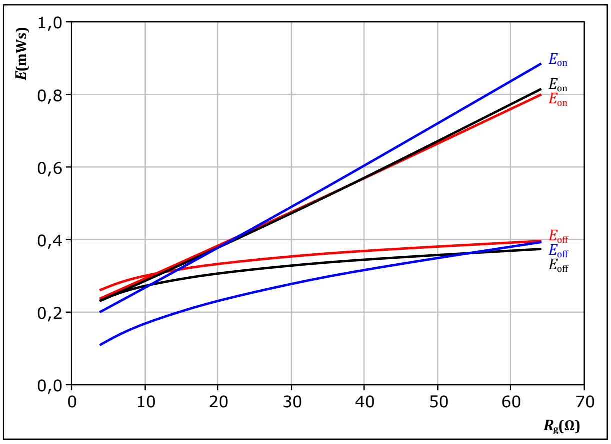
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C
R_{goff} =	16	Ω		

figure 12. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



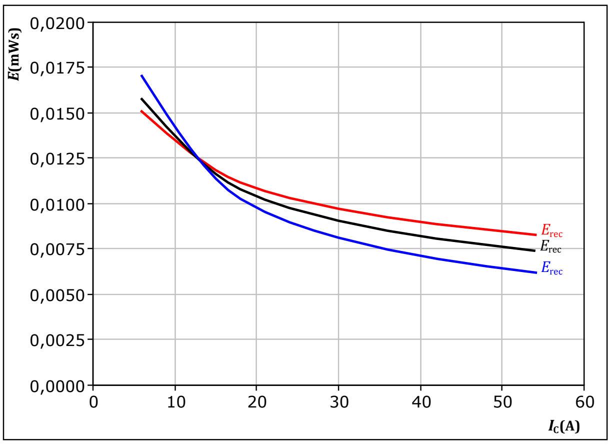
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

figure 13. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



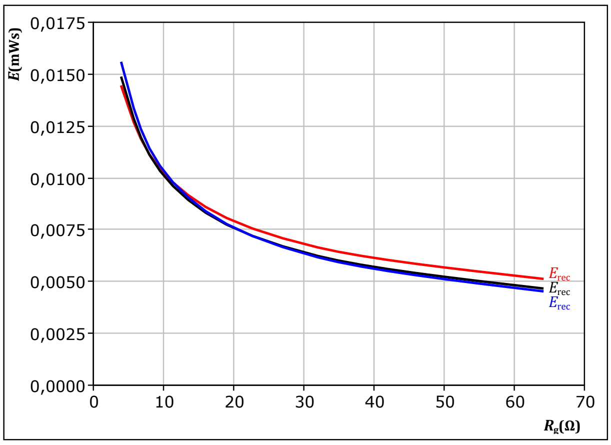
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 14. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

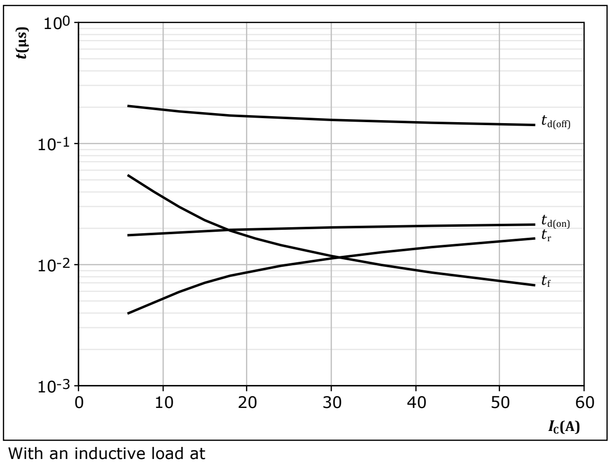
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

Boost Switching Characteristics

figure 15. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



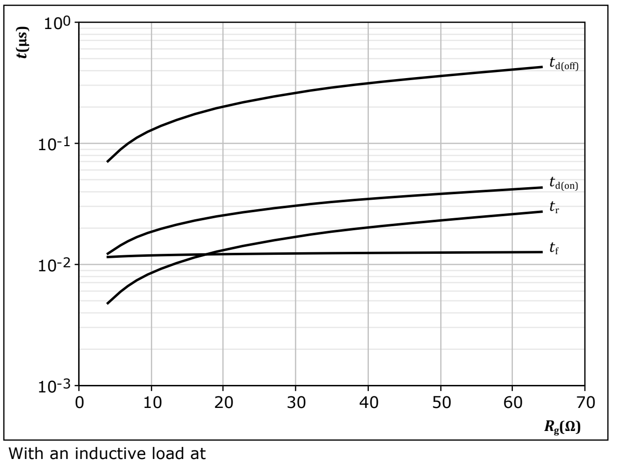
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 16. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



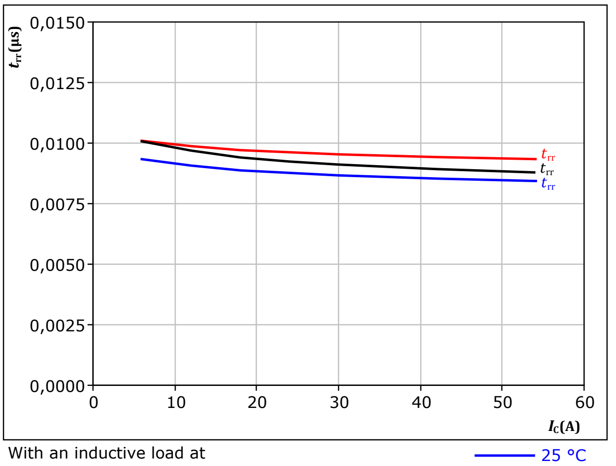
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	30	A

figure 17. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

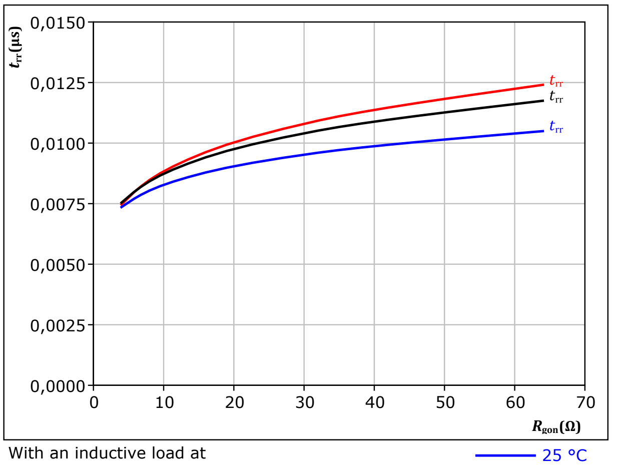
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	16	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 18. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	30	A

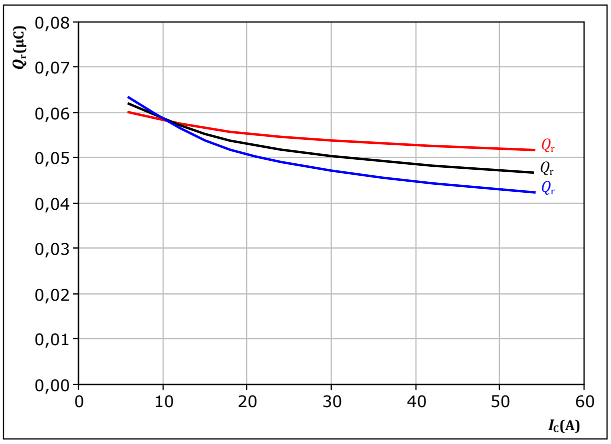
T_j: 25 °C, 125 °C, 150 °C

Boost Switching Characteristics

figure 19. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



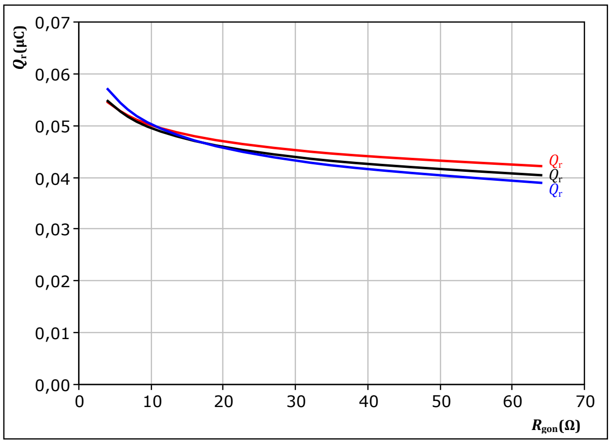
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 20. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



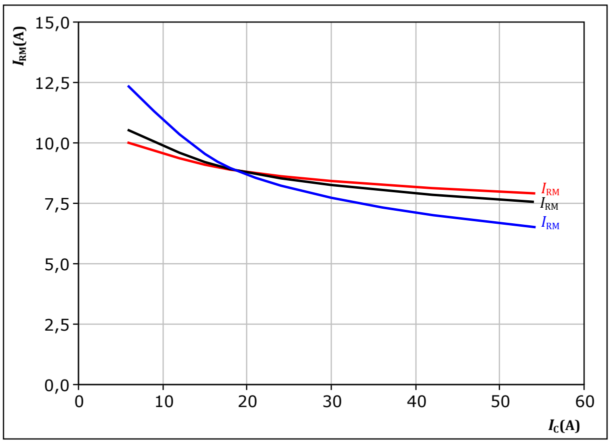
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

figure 21. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



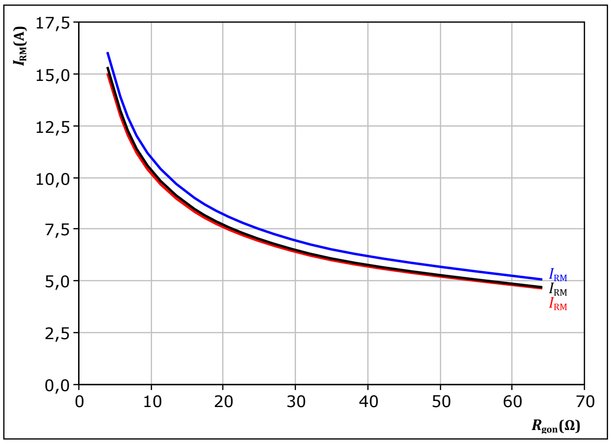
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 22. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

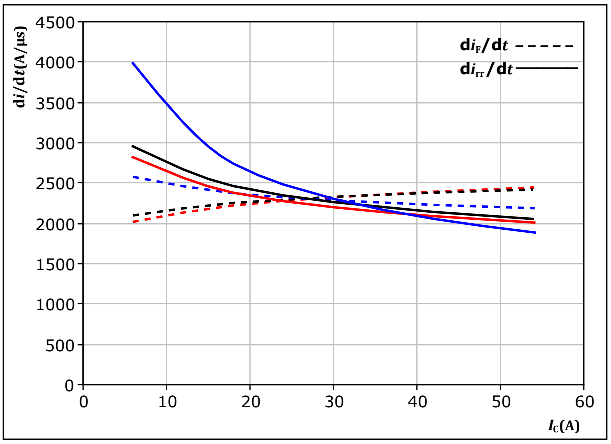
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

Boost Switching Characteristics

figure 23. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



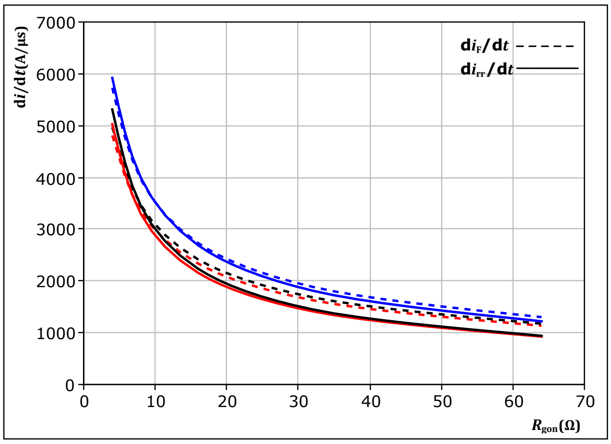
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 24. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



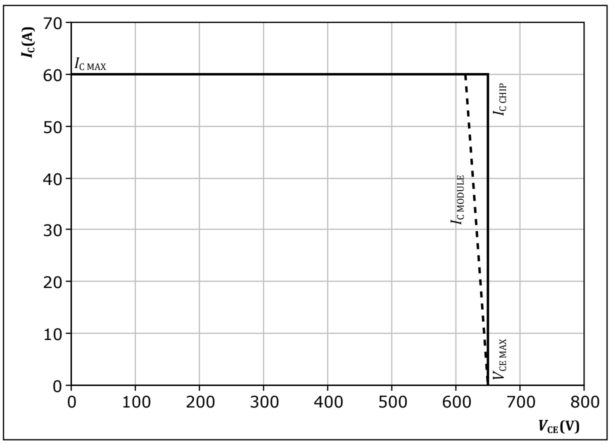
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

figure 25. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At	T_j =	150	°C
	R_{gon} =	16	Ω
	R_{goff} =	16	Ω

Boost Switching Definitions

figure 26. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} = **integrating time for** E_{off})

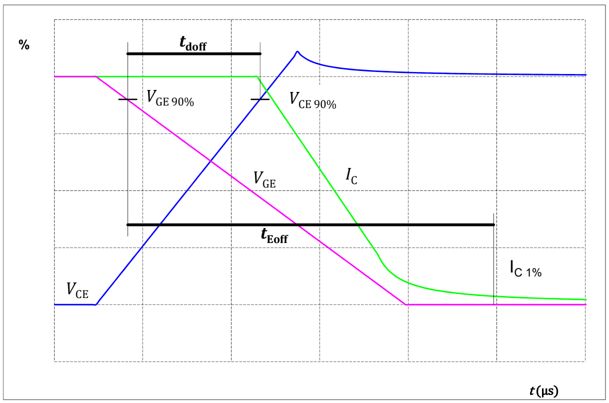


figure 27. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = **integrating time for** E_{on})

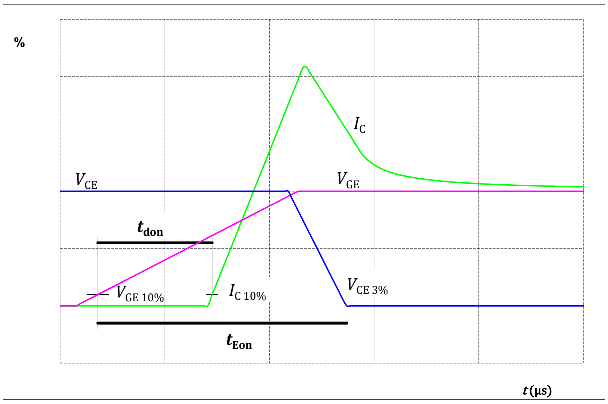


figure 28. **IGBT**

Turn-off Switching Waveforms & definition of t_f

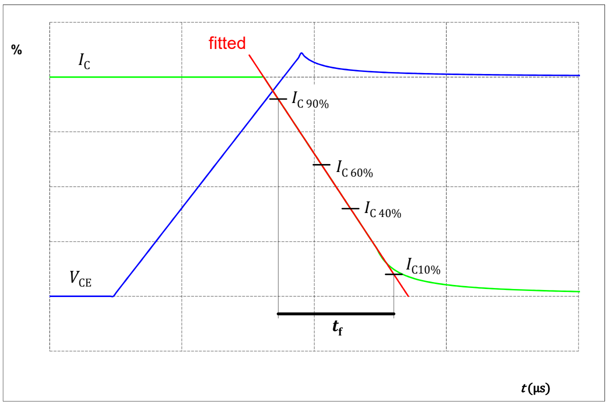
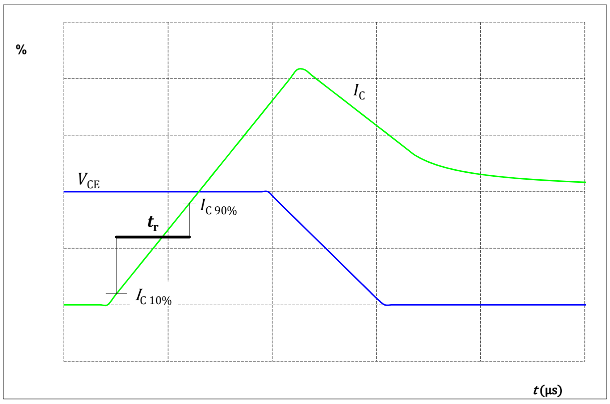


figure 29. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Boost Switching Definitions

figure 30. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

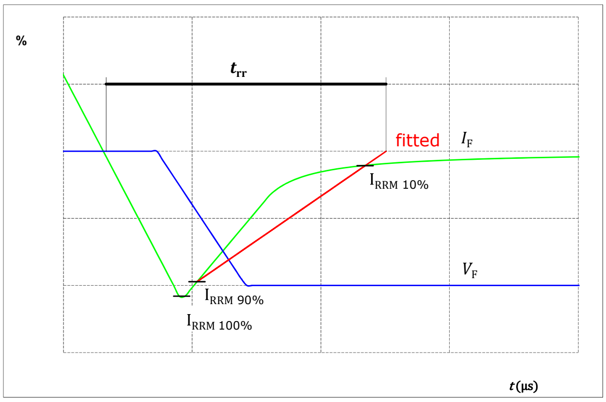
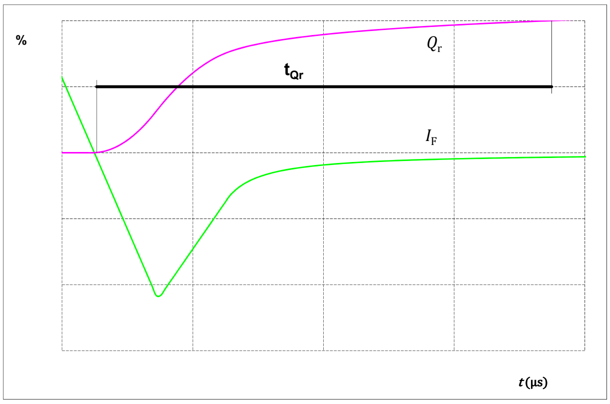


figure 31. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

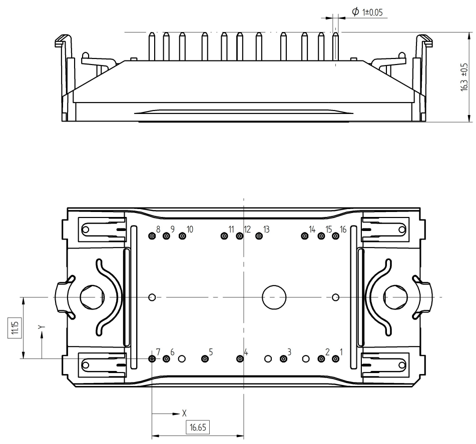
Version	Ordering Code
Without thermal paste	10-FZ073BA030SM07-M575L308
With thermal paste (5,2 W/mK, PTM6000HV)	10-FZ073BA030SM07-M575L308-/7/
With thermal paste (3,4 W/mK, PSX-P7)	10-FZ073BA030SM07-M575L308-/3/

Marking

Text	**Name**	**Date code**	**UL & VIN**	**Lot**	**Serial**
	NN-NNNNNNNNNNNNNN-TTTTTTVV	WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**	
	TTTTTTTVV	LLLLL	SSSS	WWYY	

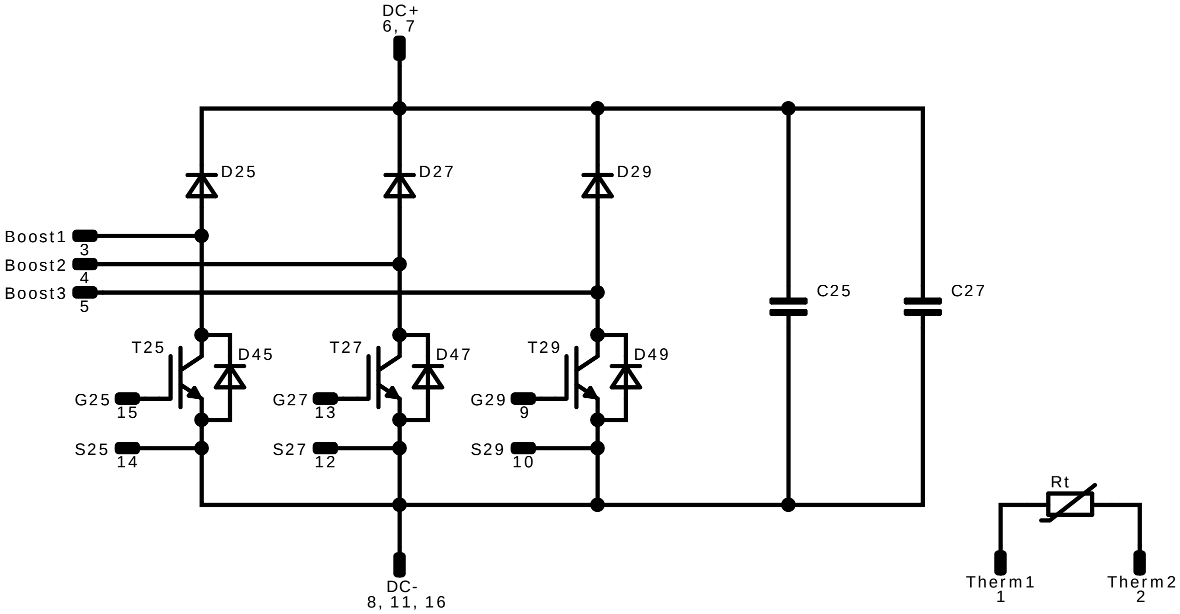
Outline

Pin table [mm]			
Pin	X	Y	Function
1	33,3	0	NTC1
2	30,7	0	NTC2
3	23,85	0	Boost3
4	15,95	0	Boost2
5	9,6	0	Boost1
6	2,6	0	DC+
7	0	0	DC+
8	0	22,3	DC-
9	2,6	22,3	G1
10	5,5	22,3	S1
11	13,1	22,3	DC-
12	15,9	22,3	S2
13	19,4	22,3	G2
14	27,7	22,3	S3
15	30,7	22,3	G3
16	33,3	22,3	DC-



Tolerance of pinpositions: ±0.5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T25, T27, T29	IGBT	650 V	30 A	Boost Switch	
D25, D27, D29	FWD	650 V	16 A	Boost Diode	
D45, D47, D49	Rectifier	1600 V	18 A	Boost Sw. Protection Diode	
C25, C27	Capacitor	630 V		Capacitor (DC)	
Rt	Thermistor			Thermistor	

Packaging instruction					
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample	

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-FZ073BA030SM07-M575L308-D2-14	13 Jul. 2022	Correct Boost Diode Maximum Ratings according to PCN-31-2022	